

1 1. A method comprising:
2 adding a liquid silicon containing precursor to
3 an etch bath for silicon nitride etching; and
4 etching silicon nitride on a wafer.

1 2. The method of claim 1 including adding a silane
2 as the silicon containing precursor.

1 3. The method of claim 2 including adding methyl
2 triethoxysilane.

1 4. The method of claim 3 including adding methyl
2 triethoxysilane to a heated bath of phosphoric acid.

1 5. The method of claim 4 including adding about .6
2 to about 2 milliliters of methyl triethoxysilane to a
3 phosphoric acid etch bath.

1 6. The method of claim 1 including adding a siloxane
2 as the silicon containing precursor.

1 7. The method of claim 1 including adding a silicon
2 containing precursor to the etch bath to obtain between
3 about 100 and about 1000 parts per million of silicon in
4 the etch bath.

1 8. A method comprising:
2 adding methyl triethoxysilane to an etch bath for
3 silicon nitride etching; and
4 etching silicon nitride on a wafer.

1 9. The method of claim 8 including adding methyl
2 triethoxysilane to a heated bath of phosphoric acid.

1 10. The method of claim 9 including adding about .6
2 to about 2 milliliters of methyl triethoxysilane to a
3 phosphoric acid etch bath.

1 11. The method of claim 8 including adding methyl
2 triethoxysilane to the etch bath to obtain between about
3 100 and about 1000 parts per million of silicon in the etch
4 bath.

1 12. A method comprising:
2 simultaneously adding wafers having a silicon
3 nitride layer to be etched and a source of silicon to a
4 nitride etching bath.

1 13. The method of claim 12 including adding a silane
2 as a source of silicon.

1 14. The method of claim 12 including adding a
2 siloxane as a source of silicon.

1 15. The method of claim 12 including adding
2 triethoxysilane to the etch bath.

1 16. The method of claim 12 including adding a silicon
2 containing precursor to the etch bath to obtain between 100
3 and 1000 parts per million of silicon in the etch bath.

1 17. The method of claim 12 including adding a liquid
2 silicon containing precursor to said etch bath.